WHAT IS CLAIMED IS:

1	1. A substrate processing chamber comprising:				
2	a chamber body;				
3	a chamber top disposed on the chamber body; and				
4	a transformer-coupled plasma generator plate within the substrate				
5	processing chamber having a plurality of transformer cores within the transformer-				
6	coupled plasma generator plate and a plurality of through holes forming conduits from				
7	a first side of the transformer-coupled plasma generator plate to a second side of the				
8	transformer-coupled plasma generator plate, a first conduit passing through a first				
9	transformer core.				
1 2	2. The substrate processing chamber of claim 1 further comprising a second conduit not passing through a transformer core.				
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1	3. The substrate processing chamber of claim 1 wherein the plasma				
2	generator plate is flat.				
1	4. The substrate processing chamber of claim 1 further comprising				
2	a second transformer core within the transformer-coupled plasma generating plate, a				
3	first primary coil being disposed to electro-magnetically couple to the first transformer				
4	core and a second primary coil being disposed to electro-magnetically couple to the				
5	second transformer core, wherein the first primary coil and the second primary coil are				
6	connected to each other in series.				
1	5. The substrate processing chamber of claim 1 wherein the toroidal				
2	transformer core comprises ferrite material.				
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1	6. The substrate processing chamber of claim 1 wherein the				
2	transformer-coupled plasma generator plate includes a dielectric spacer between the				
3	first side and the second side, and a remainder of an outer surface of the generator plate				
4	comprises an electrical conductor.				
1	7. The substrate processing chamber of claim 6 wherein the				
2	dielectric spacer is disposed within a conduit through the transformer-coupled generate				
3	plate.				

1	8. The substrate processing chamber of claim 1 further comprising				
2	an alternating-current power supply configured to operate at a frequency of about				
3	1 KHz-2 MHz.				
1	9. A substrate processing chamber comprising:				
2	a chamber body;				
3	a chamber top disposed on the chamber body;				
4	an alternating-current power supply; and				
5	a transformer-coupled plasma generator plate having a plurality of				
6	through holes forming conduits from a first side of the transformer-coupled plasma				
7	generator plate within the substrate processing chamber to a second side of the				
8	transformer-coupled plasma generator plate within the substrate processing chamber, a				
9	first portion of the conduits passing through centers of a plurality of toroidal				
10	transformer cores within the generator plate and a second portion of the conduits not				
11	passing through centers of transformer cores, the generator having a first surface				
12	comprising metal, a second surface comprising metal, and a plurality of dielectric				
13	spacers disposed between the first surface and the second surface in each of the first				
14	portion of the conduits.				
	•				
1	10. A plasma generator plate comprising:				
2	a first side;				
3	a second side;				
4	a first conduit passing from the first side to the second side through a				
5	first transformer core within the plasma generator plate;				
6	a second conduit passing from the first side to the second side through a				
7	second transformer core.				
1	11. The plasma generator plate of claim 10 further comprising a first				
2	dielectric spacer in a first secondary current path around the first transformer core.				
1	12. A method of processing a substrate in a plasma processing				
2	system, the method comprising:				
3	providing a substrate to a substrate holder in a processing chamber of the				
4	plasma processing system;				

5	flowing a plasma precursor into a multi-core transformer-coupled			
5	plasma generator;			
7	generating a plasma from the plasma precursor with the multi-core			
8	transformer coupled plasma generator; and			
9	processing the substrate.			
1 2	13. The method of claim 12 wherein the multi-core transformer-coupled plasma generator is within the processing chamber.			
1	14. The method of claim 13 wherein the multi-core transformer-			
2	coupled plasma generator is a generator plate comprising a plurality of transformer			
- 3	cores within the generator plate and a plurality of through-holes forming conduits from			
4	a first side of the generator plate to a second side of the generator plate.			
1	15. The method of claim 12 wherein plasma formed by the multi-			
2	core transformer-coupled plasma generator is coupled to the processing chamber			
3	through a conduit.			
1	16. The method of claim 15 wherein the multi-core transformer-			
2	coupled plasma generator has a first conduit passing through a first transformer core			
.3	and through a second transformer core.			
	17. The method of claim 15 wherein the multi-core transformer-			
1	coupled plasma generator has a first conduit passing through a first transformer core			
2	and a second conduit passing through a second transformer core.			
3	and a second conduit passing unough a boosta datazormon			
1	18. A plasma processing system comprising:			
2	a first substrate support structure configured to hold a first substrate in a			
.3	processing chamber;			
4	a second substrate support structure configured to hold a second			
5	substrate in the processing chamber; and			
6	a transformer-coupled plasma generator within the processing chamber			
7	disposed between the first substrate support structure and the second substrate support			
8	structure.			

1	19. The plasma processing system of claim 18 wherein the				
2	transformer-coupled plasma generator includes a toroidal transformer core.				
1	20. The plasma processing system of claim 18 wherein the plasma				
2	generator comprises a plasma generating plate having a plurality of transformer cores				
3	within the plasma generating plate and a plurality of through holes forming conduits				
4	from a first side of the plate to a second side of the plate.				
1	21. A method of simultaneously processing substrates in a plasma				
2	processing system, the method comprising:				
3	providing a first wafer and a second wafer to a processing chamber;				
4	flowing plasma precursor into the chamber;				
5	generating a plasma with a transformer-coupled plasma generator				
6	disposed between the first wafer and the second wafer; and				
7	simultaneously processing the first wafer and the second wafer.				
1	22. A plasma generator comprising:				
2	an inlet in fluid communication with;				
3	a first conduit passing through				
4	a first toroidal transformer core and through				
5	a second toroidal transformer core;				
6	a second conduit completing a plasma current circuit, in cooperation				
7	with the first conduit, around the first toroidal transformer core and around the second				
8	toroidal transformer core; and				
9	an outlet in fluid communication with the first conduit.				
1	23. A plasma generator comprising:				
2	an inlet in fluid communication with				
3	a first conduit passing through a first transformer core and with				
4	a second conduit passing through a second transformer core;				
5	a third conduit in fluid communication with the first conduit to complete				
6	a first plasma current circuit around the first transformer and in fluid communication				
7	with the second conduit to complete a second plasma current circuit around the second				
8					
_	:				

9	an outlet in fluid communication with at least the first conduit and the			
0	second conduit.			
1	24. A substrate processing system comprising:			
2	a process chamber with a chamber inlet;			
3	a chamber exhaust; and			
4	a transformer-coupled plasma generator having a first core,			
5	a first conduit passing through the first core,			
6	a second core,			
7	a second conduit passing through the second core, and			
8	a third conduit in fluid communication with the first conduit and	i		
9	the second conduit to complete a plasma current circuit path through the process			
10	chamber.			
٠	. Calain 24 wherein the third			
1	25. The substrate processing system of claim 24 wherein the third	-et		
2	conduit is a center conduit completing a first plasma current circuit path around the first			
3	core through the process chamber and the first conduit and completing a second plasma			
4	current circuit path around the second core through the process chamber and the second			
5	conduit.			
1	26. The substrate processing system of claim 24 wherein the first			
2	conduit and the second conduit comprise metal and further comprising a dielectric			
3	spacer in the plasma current circuit path.			
5	the state of the s	·		
1	27. The substrate processing system of claim 24 further comprising	3:		
2	a fourth conduit passing through			
3	a third core; and			
4	a fifth conduit passing through			
5	a fourth core.			
1	28. The substrate processing system of claim 24 further comprisin	g:		
2	a first primary coil disposed to couple electro-magnetic energy to the			
3	first core;			
4	a second primary coil disposed to couple electro-magnetic energy to t	he		
5	second core;			

6	a third primary coil disposed to couple electro-magnetic energy to the				
7	third core;				
8	a fourth primary coil disposed to couple electro-magnetic energy to the				
9	fourth core, wherein the first primary coil, the second primary coil, the third primary				
10	coil, and the forth primary coil are coupled to an AC power supply.				
1	29. The substrate processing system of claim 28 wherein the first				
2	primary coil, the second primary coil, the third primary coil, and the fourth primary coil				
3	are connected in series with the AC power supply.				
1	30. The substrate processing system of claim 28 wherein the first				
2	primary coil, the second primary coil, the third primary coil, and the fourth primary coil				
3	are connected in parallel to the AC power supply.				
1	31. A plasma generator comprising:				
2	an inlet configured to receive a plasma precursor, the inlet in fluid				
3	communication with a first plasma current path and with a second plasma current path;				
4	a first conduit passing through				
5	a first transformer core;				
6	a second conduit passing through				
7	a second transformer core, wherein the first conduit is essentially co-				
8	linear with the second conduit.				
1	32. A plasma generator comprising:				
2	an outer shell surrounding a first inner shell housing a first toroidal				
3	transformer core; and				
4	a second inner shell housing a second toroidal transformer core, wherein				
5	1.4 and 1 tours del transformer core are disnose				
6	along a common center axis.				
1	33. The plasma generator of claim 32 wherein the first inner shell is				
2	supported within the outer shell by a web allowing circulation of secondary plasma				
3	current around the first inner shell within the outer shell.				
,	V 100 A V 100				

1	3	4.	The plasma generator of claim 33 wherein the web contains an	
2	electrical lead co	lectrical lead connected to a primary coil disposed to couple electro-magnetic energy		
3	to the first toroic	dal trai	nsformer core.	
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1	_		The plasma generator of claim 32 wherein the first inner shell	
2	includes a shape	ed bott	om portion to provide a circular cross-section to the inner shell.	
1	3	36.	The plasma generator of claim 32 further comprising:	
2	а	an inlet; and		
3	a a	an outlet, both the inlet and the outlet lying along the common center		
4	axis.			
1	3	37.	An ion implantation system comprising:	
2		an ion	source having a toroidal plasma generator, and	
3			source aperture aligned essentially along a center line of the	
4	toroidal plasma generator.			
		. 0	The ion implantation system of claim 37 further comprising a	
1		38. -14	•	
2		raction electrode disposed to accelerate ions from the ion source toward a		
3	second extraction	on elec	ctrode.	
1	:	39.	The ion implantation system of claim 37 wherein the toroidal	
2	plasma generator includes a first core and a second core, the first core and the second			
3	core being aligned essentially along a center line of the toroidal plasma generator.			
1		40.	A method of providing ions to an ion implantation system, the	
2	method compri	ising:	•	
3		provid	ling an ion precursor to a transformer-coupled toroidal plasma	
4	generator in an	ion so	ource;	
5		ionizii	ng at least a portion of the ion precursor into ions, the ions having	
6	a greater density at a center of the transformer-coupled toroidal plasma generator and			
7	extending alon	g a lin	e through the center of the transformer-coupled toroidal plasma	
8	generator; and			
9		ejectir	ng a portion of the ions out of the ion source.	

1	41.	A plasma torch nead comprising:		
2		er nozzle;		
3	an inner nozzle, the inner nozzle including a conduit passing through the			
4	inner nozzle from an	inner nozzle from an inlet side toward an outlet,		
5		dal transformer core surrounding the conduit; and		
6	a bypa	ss providing a return path for a secondary plasma current circuit		
7	around the toroidal transformer core.			
	40	The plasma torch head of claim 41 wherein the inner nozzle		
1	42.			
2	comprises metal and further including a dielectric spacer in the inner nozzle to prevent			
3	an electric path throu	gh the inner nozzle around the toroidal transformer core.		
1	43.	The plasma torch head of claim 41 wherein a first gas is flown		
2	through the conduit	and a second gas if flown through the bypass, the first gas being		
3	different from the se			
		my the state of aloing 42 wherein the first gas is		
1	44.	The plasma torch head of claim 43 wherein the first gas is		
2	oxygen and the seco	nd gas is either propane or hydrogen.		
1	45.	The plasma torch head of claim 41 further comprising a primary		
2	coil disposed to cou	ple electro-magnetic energy to the toroidal transformer core		
3	wherein the primary coil and the toroidal transformer core are enclosed within the inner			
4	nozzle.	and the second of the second second of the second s		
		A method of cutting material using a plasma torch, the method		
1	46.	A method of cutting material using a plasma toron, the mount		
2	comprising:	1 '44'		
3		ing a plasma precursor in a conduit through a center of a toroidal		
4	transformer core of a plasma generator in an inner nozzle of a plasma torch;			
5		ning plasma from the plasma precursor;		
6	com	pleting a plasma current secondary circuit around the toroidal		
7	•			
8	trans	sporting plasma out an outlet of the plasma torch.		
1	47.	The method of claim 46 further comprising flowing carrier gas		
2	through the bypass			

l	2	18.	The method of claim 40 wherein the forming plasma step	
2	includes provid	ing a p	rimary voltage to a primary coil coupling electro-magnetic	
3	energy to the toroidal transformer core, the primary voltage being an alternating-current			
4	voltage less than about 115 Volts.			
1	4	49.	An ion source for an ion milling apparatus, the ion source	
2	comprising:			
3		a transf	former-coupled toroidal plasma generator (having a primary coil	
4			ctro-magnetic energy to a toroidal core, the transformer-coupled	
5	toroidal plasma generator disposed to provide plasma along a center line of the			
6 .			oroidal plasma generator toward an accelerator plate.	
1		50.	The ion source of claim 1 wherein the transformer-coupled	
2	toroidal plasma	gener	ator further includes a second toroidal core.	
1	•	51.	A method for providing ions to an ion milling apparatus, the	
2	method compri	ising:		
3	-	provid	ing an ion precursor to a transformer-coupled toroidal plasma	
4	generator;	,		
5	,	ionizin	g at least a portion of the ion precursor to form ions, the ions	
6			ong a center axis of the transformer-coupled toroidal plasma	
7	generator; and			
8	•	ejectio	n a portion of the ions toward an accelerator plate.	
1		52.	The method of claim 51 wherein the ion precursor forms reactive	
2	ions	- 		